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## **FDD6N25** N-Channel UniFET<sup>TM</sup> MOSFET 250 V, 4.4 A, 1.1 Ω

### Features

- $R_{DS(on)}$  = 1.1  $\Omega$  (Max.) @ V<sub>GS</sub> = 10 V, I<sub>D</sub> = 2.2 A
- Low Gate Charge (Typ. 4.5 nC)
- Low C<sub>rss</sub> (Typ. 5 pF)
- 100% Avalanche Tested

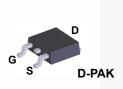
#### Applications

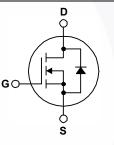
- LCD/LED/PDP TV
- Consumer Appliances
- Lighting
- Uninterruptible Power Supply
- AC-DC Power Supply

FDD6N25 — N-Channel UniFET<sup>TM</sup> MOSFET

## Description

UniFET<sup>TM</sup> MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





#### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter			FDD6N25TM	Unit	
V <sub>DSS</sub>	Drain-Source Voltage			250	V	
ID	Drain Current	- Continuous (T <sub>C</sub> = 25°C) - Continuous (T <sub>C</sub> = 100°C)		4.4 2.6	A A	
I <sub>DM</sub>	Drain Current	- Pulsed	(Note 1)	18	А	
V <sub>GSS</sub>	Gate-Source voltage			±30	V	
E <sub>AS</sub>	Single Pulsed Avalanche Energy			45	mJ	
I <sub>AR</sub>	Avalanche Current			4.4	Α	
E <sub>AR</sub>	Repetitive Avalanche Energy (N			5	mJ	
dv/dt	Peak Diode Recovery	dv/dt	(Note 3)	4.5	V/ns	
P <sub>D</sub>	Power Dissipation	(T <sub>C</sub> = 25°C) - Derate Above 25°C		50 0.4	W W/°C	
T <sub>J,</sub> T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +150	°C	
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			300	°C	

#### **Thermal Characteristics**

Symbol	Parameter	FDD6N25TM	Unit	
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max. 2.5			
$R_{\thetaJA}$	Thermal Resistance, Junction-to-Ambient, Max.	110	°C/W	

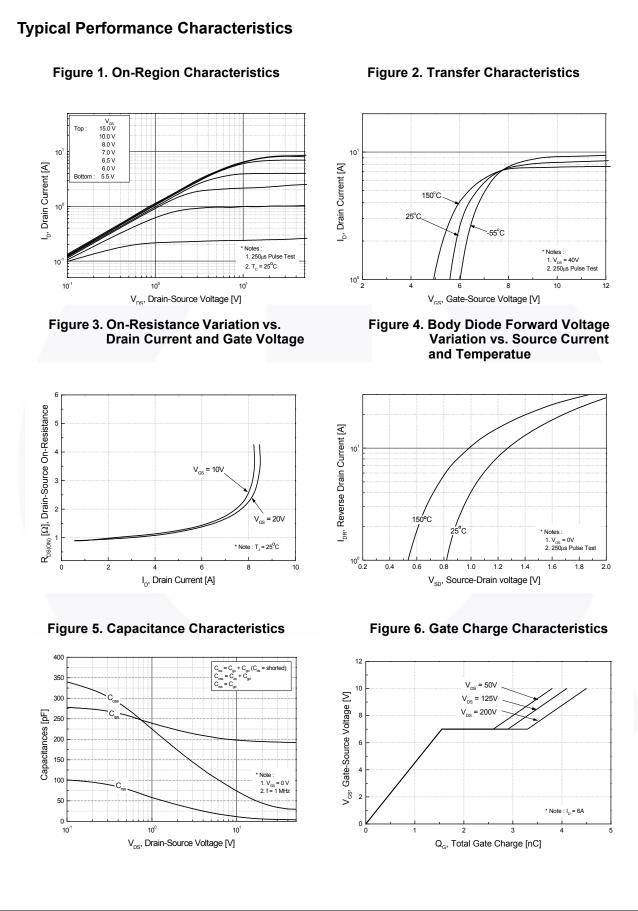
FDD6N25
- N-Channel
I UniFET <sup>TM</sup>
MOSFET

		Top Mark	Package	ckage Packing Method Reel Size		Та	pe Width	Qu	antity
		DPAK	PAK Tape and Reel 330 mm		16 mm		2500 units		
Electric	al Chara	acteristics T <sub>c</sub> = 2	25°C unless o	therwise noted.					
Symbol		Parameter		Conditions		Min.	Тур.	Max	Unit
Off Charac	teristics								<u> </u>
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage		V <sub>GS</sub> =	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA					V
$\Delta BV_{DSS}$ / $\Delta T_{J}$	Breakdown Voltage Temperature Coefficient		I <sub>D</sub> = 25	$I_D = 250 \ \mu$ A, Referenced to 25°C			0.25		V/∘C
I <sub>DSS</sub>	Zero Gate	Voltage Drain Current		$V_{DS} = 250 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 200 \text{ V}, T_{C} = 125^{\circ}\text{C}$				1 10	μΑ μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward		-	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V				100	nA
I <sub>GSSR</sub>	Gate-Body	Leakage Current, Reve	rse V <sub>GS</sub> =	-30 V, V <sub>DS</sub> = 0 V				-100	nA
On Charac	teristics								
V <sub>GS(th)</sub>	Gate Threshold Voltage		V <sub>DS</sub> =	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA		3.0		5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance		V <sub>GS</sub> =	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2.2 A			0.9	1.1	Ω
9 <sub>FS</sub>	Forward Transconductance		V <sub>DS</sub> =	V <sub>DS</sub> = 40 V, I <sub>D</sub> = 2.2 A			5.5		S
Dynamic C	haracterist	ics					•		
C <sub>iss</sub>				$V_{DS} = 25 V, V_{GS} = 0 V,$ f = 1 MHz			194	250	pF
C <sub>oss</sub>			f = 1 N				38	50	pF
C <sub>rss</sub>						5	8	pF	
Switching	Characteris	itics							
t <sub>d(on)</sub>	Turn-On D	elay Time		$V_{DD} = 125 \text{ V}, \text{ I}_{D} = 6 \text{ A},$ $V_{GS} = 10 \text{ V}, \text{ R}_{G} = 25 \Omega$			10	30	ns
t <sub>r</sub>	Turn-On R	ise Time	V <sub>GS</sub> =				25	60	ns
t <sub>d(off)</sub>	Turn-Off D	elay Time					7	24	ns
t <sub>f</sub>	Turn-Off Fa	all Time			(Note 4)		12	34	ns
Qg	Total Gate	Charge	V <sub>DS</sub> =	$V_{DS} = 200 \text{ V}, \text{ I}_{D} = 6 \text{ A},$ $V_{GS} = 10 \text{ V}$ (Note 4)			4.5	6	nC
Q <sub>gs</sub>	Gate-Sour	ce Charge	V <sub>GS</sub> =				1.5		nC
Q <sub>gd</sub>	Gate-Drain	Charge					1.8		nC
	rce Diode C	haracteristics and Max	imum Rating	js					
I <sub>S</sub>	Maximum Continuous Drain-Source Dio			ard Current				4.4	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode F			Current				18	Α
V <sub>SD</sub>	Drain-Sour	ce Diode Forward Voltag	ge V <sub>GS</sub> =	0 V, I <sub>S</sub> = 4.4 A				1.4	V
t <sub>rr</sub>	Reverse R	ecovery Time		0 V, I <sub>S</sub> = 6 A,			145		ns
Q <sub>rr</sub>	Reverse R	ecovery Charge	dI <sub>F</sub> /dt	dI <sub>F</sub> /dt =100 A/µs			0.55		μC

#### Notes:

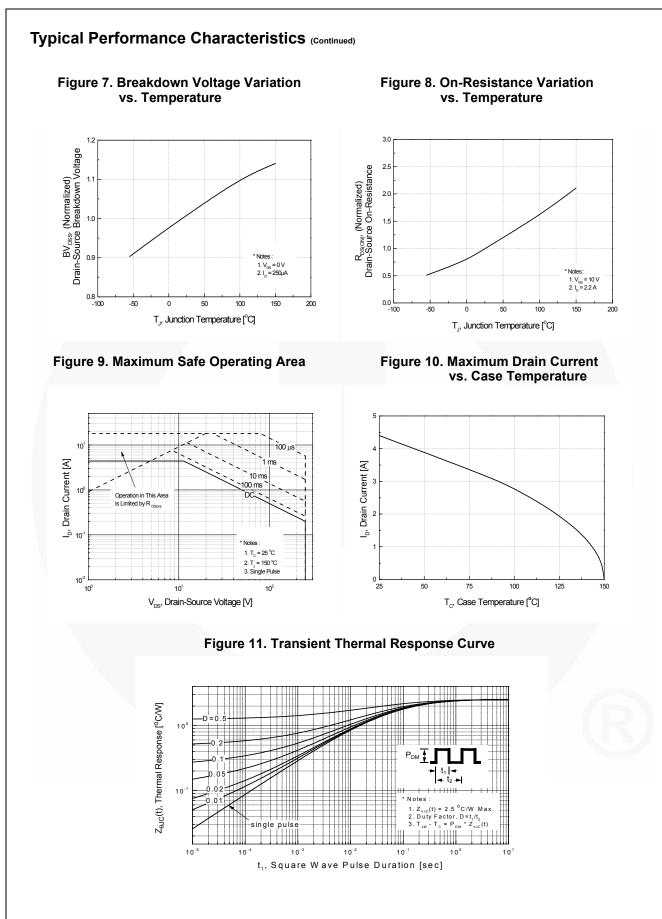
1. Repetitive rating: pulse-width limited by maximum junction temperature.

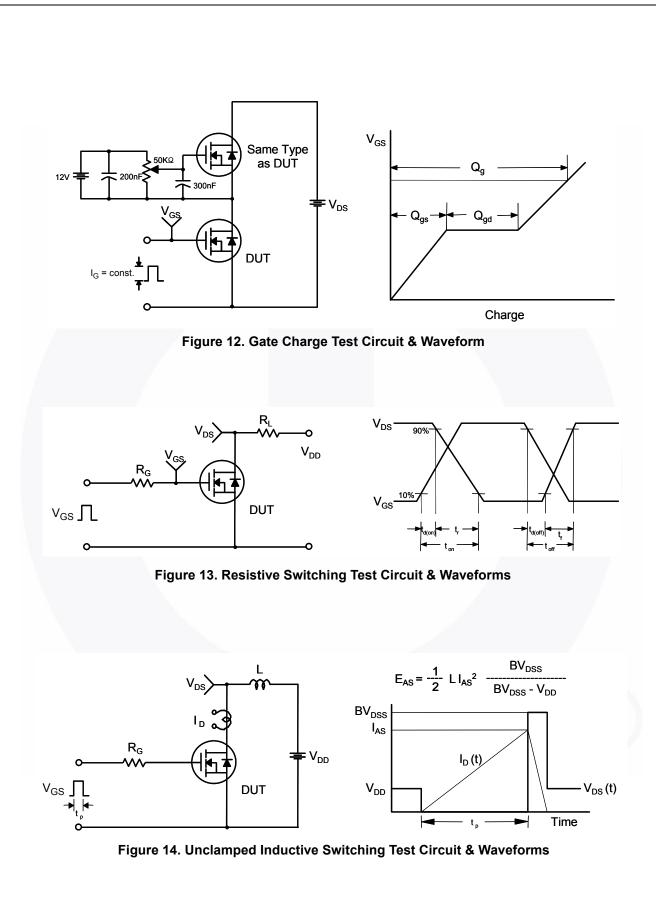
2. L = 3.7 mH, I<sub>AS</sub> = 4.4 A, V<sub>DD</sub> = 50 V, R<sub>G</sub> = 25  $\Omega$ , starting T<sub>J</sub> = 25°C. 3. I<sub>SD</sub> = 4.4 A, di/dt ≤ 200 A/µs, V<sub>DD</sub> = SV<sub>DSS</sub>, starting T<sub>J</sub> = 25°C. 4. Essentially independent of operating temperature typical characteristics.



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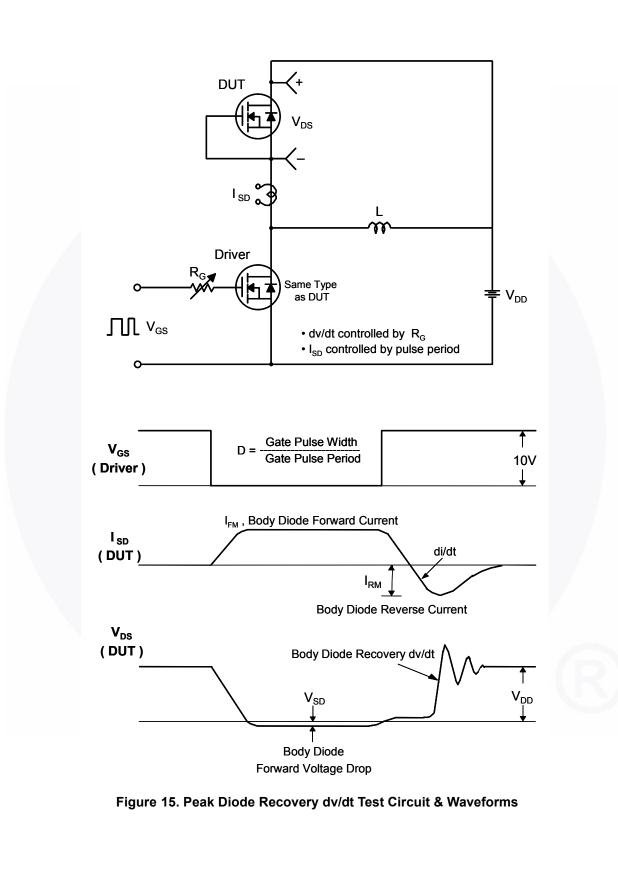
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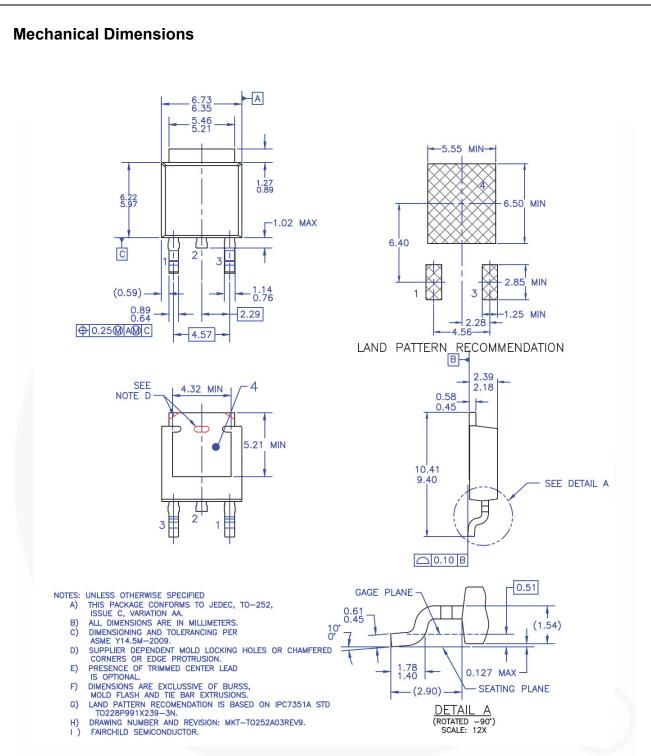




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#### Figure 16. TO252 (D-PAK), Molded, 3-Lead, Option AA&AB

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